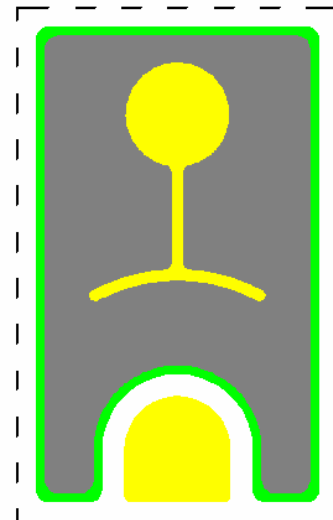


✧ Features:

- Long lifetime and high reliability
- Stress reduced EPI structure
- High radiant flux
- 100% testing and sorting
- High ESD withstand voltage

S1016 chip top view

✧ Physical Characteristics:

Structure	InGaN MQW
Chip Size	250±25μm × 400±25μm
Chip Thickness	85 ± 10 μm
Electrode Size	82 ± 5 μm
Electrode Metal	Au alloy
Packaging	19 cm×19 cm blue tape medium tack

✧ Part Number Definition:
IvL-Sab-Cx-Lyy-ZZZ

- IvL:** Company abbreviation
Sab: Chip size, a-chip length, b-chip width
Cx: Dominant wavelength, color bin
Lyy: Luminous intensity bin
ZZZ: IvL product serial number

✧ Optical and Electrical Characteristics (Ta = RT, If= 20mA, Vr= -5V)

Part Number	Dominant Wavelength (λd, nm)	Luminous Intensity (X, mcd)	Reverse Current (Ir, μA) Max
IvL-Sab-Cx-Lyy-ZZZ	Cx	Lyy	2

✧ Wavelength Bins:

Purple Blue	P1	P2	P3	P4	P5	P6	P7	P8
Min	445.0	447.5	450.0	452.5	455.0	457.5	460.0	462.5
Max	447.5	450.0	452.5	455.0	457.5	460.0	462.5	465.0

✧ Forward Voltage Bins:

	V28	V30	V32	V34
Min	2.6	2.8	3.0	3.2
Max	2.8	3.0	3.2	3.4

✧ Luminous Intensity Bins:

	L01	L02	L03	L04	L05	L06	L07	L08	L09	L10	L11	L12
Min	50.0	60.0	70.0	80.0	90.0	105.0	120.0	140.0	160.0	190.0	220.0	250.0
Max	59.9	69.9	79.9	89.9	104.9	119.9	139.9	159.9	189.9	219.9	249.9	284.9

✧ Notes:

- 1) Recommended clear epoxy for die mounting to optimize light output.
- 2) Assembly processing temperature must not exceed 280°C for 10 sec.
- 3) GaN LEDs are ESD sensitive. Please observe appropriate precautions during handling and processing. For further information please refer to MIL-STD-1686A.
- 4) All parameters are measured using InvenLux's tester on bare chips, mcd values will vary +10 to - 0%.